

Pb Free Plating Product

## ES3A thru ES3M



3 Ampere Surface Mount Type Super Fast Recovery Rectifier Diodes

### FEATURE

- ◆ Glass passivated chip junction
- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Low reverse leakage
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed:  
250°C/10 seconds at terminals

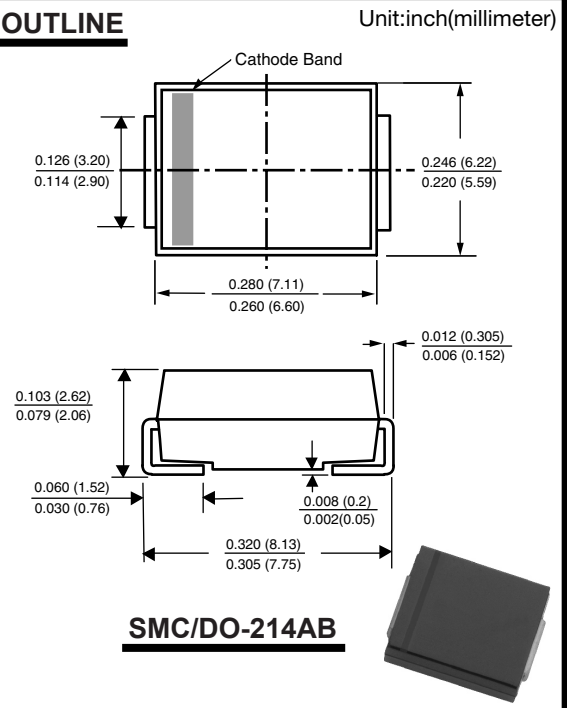
### MECHANICAL DATA

**Case:** SMC/DO-214AB Package  
**Terminals:** Solder plated, solderable per MIL-STD-750, Method 2026  
**Polarity:** Color band denotes cathode band  
**Mounting Position:** Any  
**Weight:** 0.22 gram approximately

### APPLICATION

- ◆ LED SMPS/Industrial power supply
- ◆ HID ballast stabilizer
- ◆ Telecommunication SMPS/LED street lamp

### OUTLINE



### Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half-wave, 60 Hz, resistive or inductive load, for capacitive load derate current by 20%.

Parameter	Symbols	ES3A	ES3B	ES3C	ES3D	ES3F	ES3G	ES3J	ES3K	ES3M	Units	
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	150	200	300	400	600	800	1000	V	
Maximum RMS Voltage	$V_{RMS}$	35	70	105	140	210	280	420	560	700	V	
Maximum DC Blocking Voltage	$V_{DC}$	50	100	150	200	300	400	600	800	1000	V	
Maximum Average Forward Current	$I_{F(AV)}$	3									A	
Peak Peak Forward Surge Current, 8.3 ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	$I_{FSM}$	100									A	
Maximum Forward Voltage at $I_F = 3 A$	$V_F$	0.95			1.3			1.7			V	
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_A = 25^\circ C$ $T_A = 100^\circ C$	$I_R$	10					500					$\mu A$
Maximum Reverse Recovery Time <sup>1)</sup>	$t_{rr}$	35									ns	
Typical Junction Capacitance <sup>2)</sup>	$C_J$	50				40						pF
Junction Temperature Range	$T_J$	- 55 to + 150										°C
Storage temperature range	$T_s$	- 55 to + 150										°C

<sup>1)</sup> Reverse recovery test conditions:  $I_F = 0.5 A$ ,  $I_R = 1 A$ ,  $I_{rr} = 0.25 A$

<sup>2)</sup> Measured at 1 MHz and applied reverse voltage of 4 V D.C.

## RATINGS AND CHARACTERISTIC CURVES ES3A thru ES3M

FIG.1 - REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

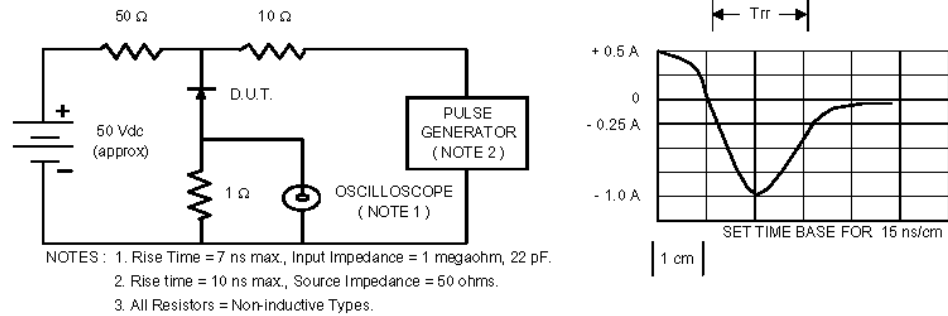


FIG.2 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

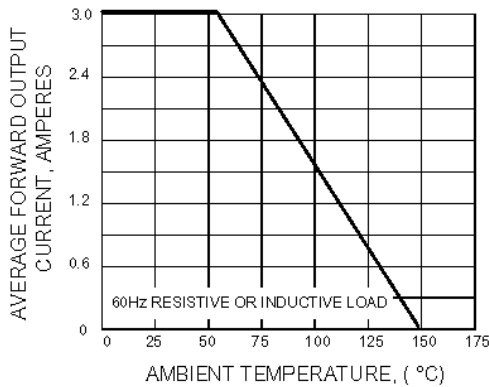


FIG.3 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

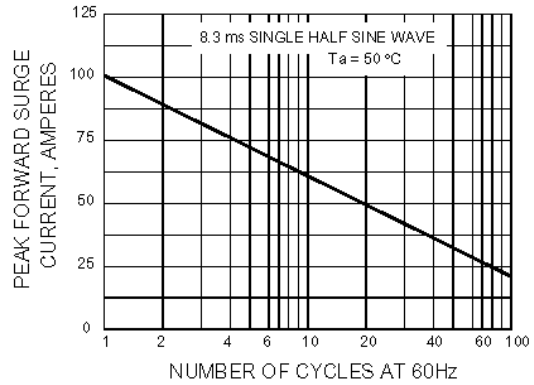


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

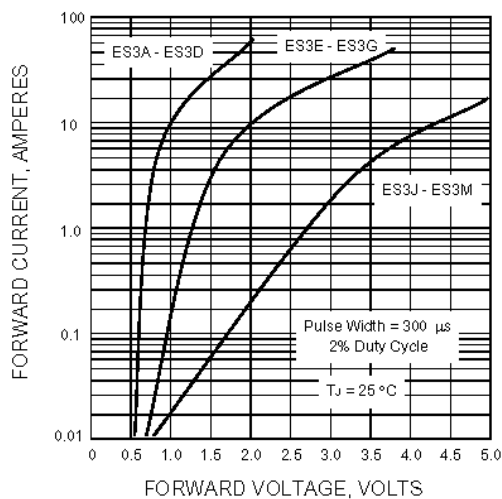


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

